

# **MBR0520LT1, MBR0520LT3**

Preferred Devices

# **Surface Mount Schottky Power Rectifier**

## Plastic SOD-123 Package

The Schottky Power Rectifier employs the Schottky Barrier principle with a barrier metal that produces optimal forward voltage drop—reverse current tradeoff. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system. This package provides an alternative to the leadless 34 MELF style package. These state—of—the—art devices have the following features:

#### **Features**

- Guardring for Stress Protection
- Very Low Forward Voltage (0.38 V Max @ 0.5 A, 25°C)
- 125°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Package Designed for Optimal Automated Board Assembly
- Pb-Free Packages are Available

#### **Mechanical Characteristics**

- Reel Options: MBR0520LT1 = 3,000 per 7'' reel/8 mm tapeMBR0520LT3 = 10,000 per 13'' reel/8 mm tape
- Polarity Designator: Cathode Band
- Weight: 11.7 mg (approximately)
- Case: Epoxy, Molded
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

# SCHOTTKY BARRIER RECTIFIER 0.5 AMPERES, 20 VOLTS



SOD-123 CASE 425 STYLE 1

#### **MARKING DIAGRAM**



## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	20	V
Average Rectified Forward Current (Rated V <sub>R</sub> , T <sub>L</sub> = 90°C)	I <sub>F(AV)</sub>	0.5	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	5.5	А
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C
Operating Junction Temperature	TJ	-65 to +125	°C
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	1000	V/μs
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance; Junction-to-Ambient (Note 1)	$R_{ heta JA}$	206	°C/W
Thermal Resistance; Junction-to-Lead	$R_{ heta JL}$	150	°C/W

## **ELECTRICAL CHARACTERISTICS**

Maximum Instantaneous Forward Voltage (Note 2)	٧F	$T_J = 25^{\circ}C$	T <sub>J</sub> = 100°C	V
$(i_F = 0.1 \text{ Amps})$ $(i_F = 0.5 \text{ Amps})$	·	0.300 0.385	0.220 0.330	
Maximum Instantaneous Reverse Current (Note 2)	I <sub>R</sub>	T <sub>J</sub> = 25°C	T <sub>J</sub> = 100°C	mA
(V <sub>R</sub> = 10 V) (Rated DC Voltage = 20 V)		75 μΑ 250 μΑ	5 mA 8 mA	

 <sup>1. 1</sup> inch square pad size (1 x 0.5 inch for each lead) on FR4 board.
2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

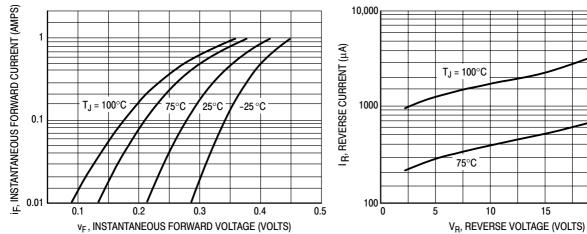


Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

15

20

25

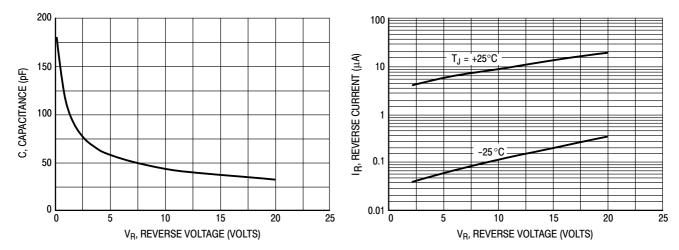


Figure 3. Typical Capacitance

**Figure 4. Typical Reverse Current** 

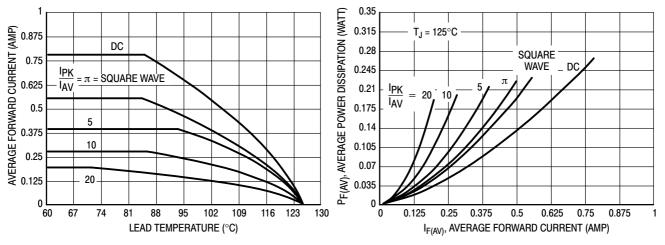


Figure 5. Current Derating (Lead)

Figure 6. Power Dissipation